QS5U36

1.5V Drive Nch+SBD MOSFET

V_{DSS}	20V
$R_{DS(on)}$(Max.)	133mΩ
I_D	±2.5A
P_D	1.25W

●**Outline**

TSMT5

●**Inner circuit**

(1) Gate
(2) Source
(3) Anode
(4) Cathode
(5) Drain

*1 ESD Protection Diode
*2 Body Diode

●**Features**

1) The QS5U36 combines Nch MOSFET with a Schottky barrier diode in a single TSMT5 package.
2) High-speed switching, Low On-resistance.
3) Low voltage drive (1.5V drive).
4) Built-in Low V_F schottky barrier diode.
5) Pb-free lead plating ; RoHS compliant.

●**Application**
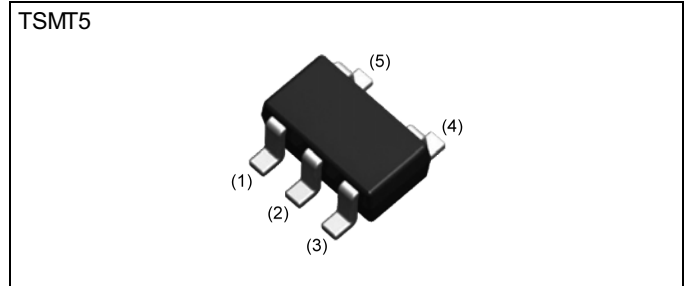
Switching

●**Packaging specifications**

Type	Packing	Embossed Tape
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3000
	Taping code	TR
	Marking	U36

●**Absolute maximum ratings** ($T_a = 25°C$)

<MOSFET>

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	20	V
Gate - Source voltage	V_{GSS}	±10	V
Continuous drain current	I_D	±2.5	A
Pulsed drain current	$I_{D, pulse}$[*1]	±5.0	A
Continuous source current (body diode)	I_S	0.7	A
Pulsed source current (body diode)	$I_{S, pulse}$[*1]	5.0	A
Power dissipation	P_D[*3]	0.9	W/element
Junction temperature	T_j	150	°C

● **Absolute maximum ratings** (T_a = 25°C)

<SBD>

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RM}	25	V
Reverse voltage	V_R	20	V
Forward current	I_F	0.7	A
Forward current surge peak	I_{FSM}[*2]	3.0	A
Power dissipation	P_D[*3]	0.7	W/element
Junction temperature	T_j	150	°C

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Parameter	Symbol	Value	Unit
Power dissipation	P_D[*3]	1.25	W/total
Range of storage temperature	T_{stg}	-55 to +150	°C

● **Electrical characteristics** (T_a = 25°C)

<MOSFET>

Parameter	Symbol	Conditions	Values Min.	Values Typ.	Values Max.	Unit
Gate - Source leakage current	I_{GSS}	V_{GS} = ±10V, V_{DS} = 0V	-	-	±10	μA
Drain - Source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 1mA	20	-	-	V
Zero gate voltage drain current	I_{DSS}	V_{DS} = 20V, V_{GS} = 0V	-	-	1	μA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} = 10V, I_D = 1mA	0.3	-	1.3	V
Static drain - source on - state resistance	$R_{DS(on)}$[*4]	V_{GS} = 4.5V, I_D = 2.5A	-	58	81	mΩ
		V_{GS} = 2.5V, I_D = 2.5A	-	74	104	
		V_{GS} = 1.8V, I_D = 1.3A	-	95	133	
		V_{GS} = 1.5V, I_D = 0.5A	-	120	240	
Transconductance	g_{fs}[*4]	V_{DS} = 10V, I_D = 2.5A	2.7	-	-	S

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● **Electrical characteristics** (T_a = 25°C)

<MOSFET>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	V_{GS} = 0V	-	280	-	pF
Output capacitance	C_{oss}	V_{DS} = 10V	-	65	-	
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	35	-	
Turn - on delay time	$t_{d(on)}$[4]	$V_{DD} \simeq$ 10V, V_{GS} = 4.5V	-	6	-	ns
Rise time	t_r[4]	I_D = 1.3A	-	15	-	
Turn - off delay time	$t_{d(off)}$[4]	R_L = 7.7Ω	-	30	-	
Fall time	t_f[4]	R_G = 10Ω	-	15	-	

● **Gate charge characteristics** (T_a = 25°C)

<MOSFET>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g[4]	$V_{DD} \simeq$ 10V, I_D = 2.5A V_{GS} = 4.5V	-	3.5	-	nC
Gate - Source charge	Q_{gs}[4]		-	0.8	-	
Gate - Drain charge	Q_{gd}[4]		-	0.7	-	

● **Body diode electirical characteristics** (Source-Drain) (T_a = 25°C)

<MOSFET>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_{SD}[4]	V_{GS} = 0V, I_S = 0.7A	-	-	1.2	V

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● **Electrical characteristics** (T_a = 25°C)

<SBD>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 0.7A	-	-	0.49	V
Reverse current	I_R	V_R = 20V	-	-	200	μA

*1 Pw ≤ 10μs, Duty cycle ≤ 1%

*2 60Hz·1 cycle

*3 Mounted on a ceramic board

*4 Pulsed

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● **Electrical characteristic curves <MOSFET>**

Fig.1 Typical Capacitance vs. Drain - Source Voltage
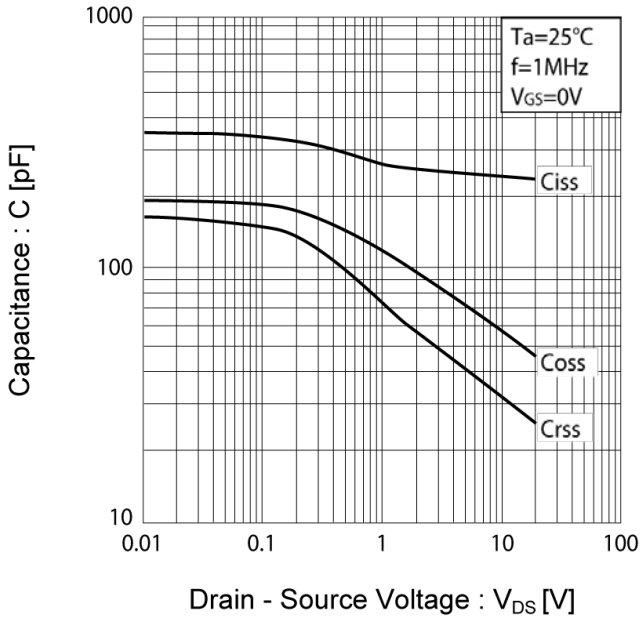
Fig.2 Switching Characteristics
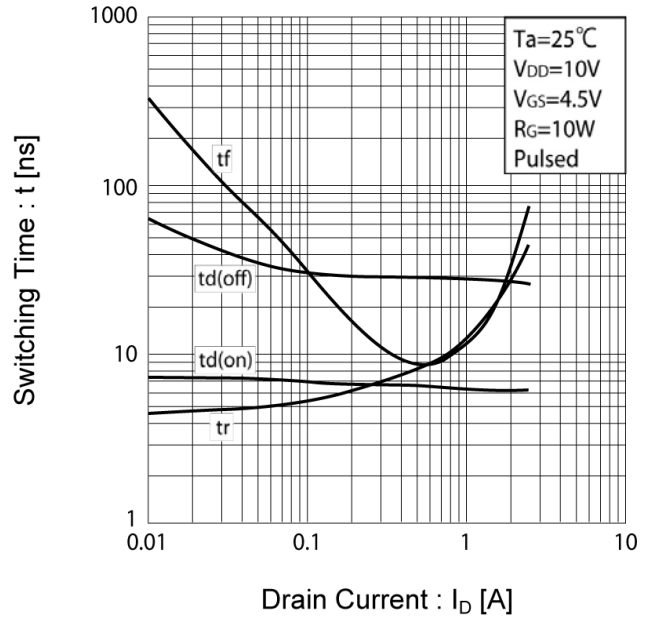
Fig.3 Dynamic Input Characteristics
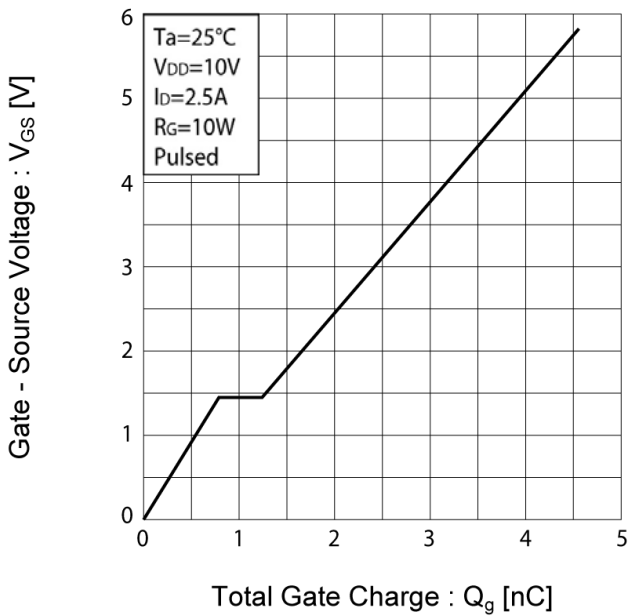
Fig.4 Typical Transfer Characteristics

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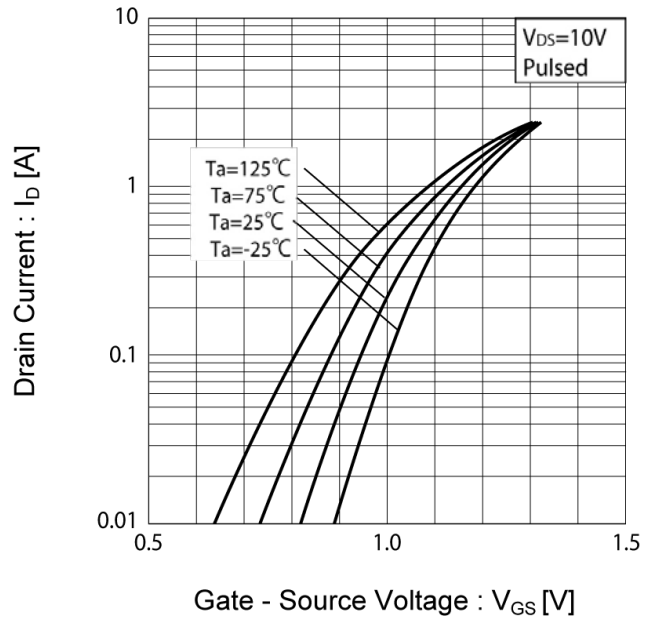
● **Electrical characteristic curves <MOSFET>**

Fig.5 Static Drain - Source On - State
Resistance vs. Gate Source Voltage
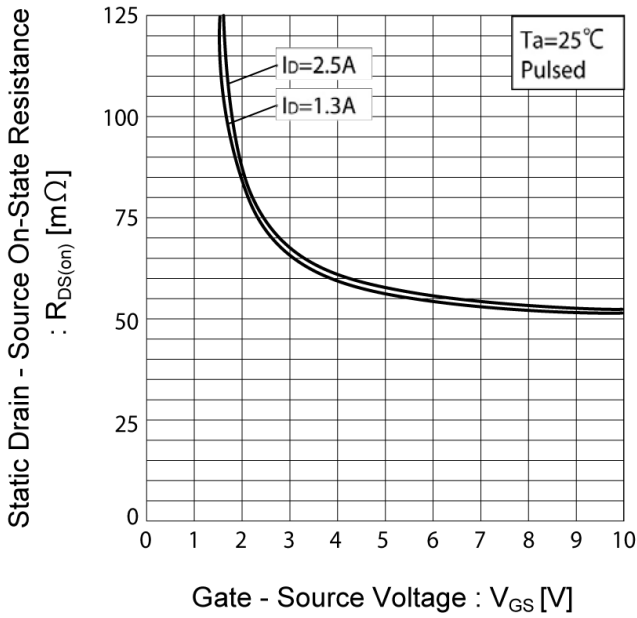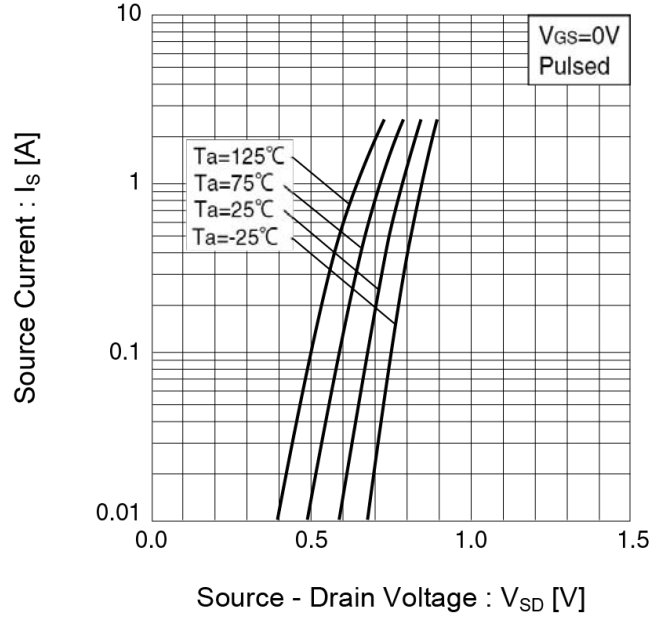
Fig.6 Source Current vs. Source Drain
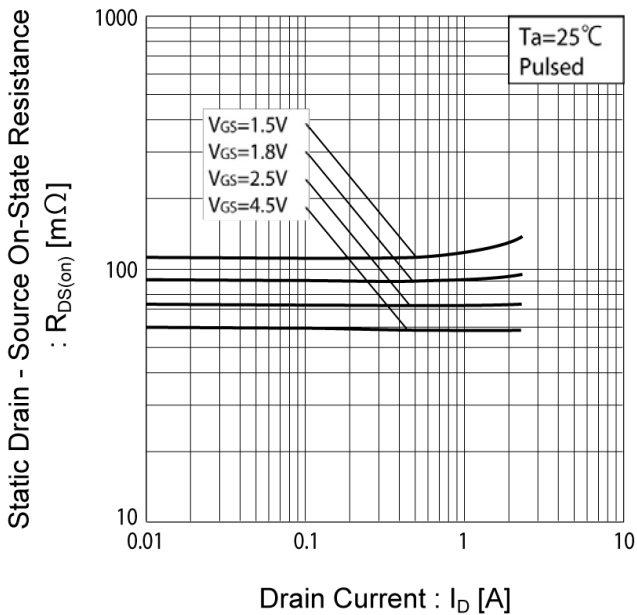Voltage

Fig.7 Static Drain - Source On - State
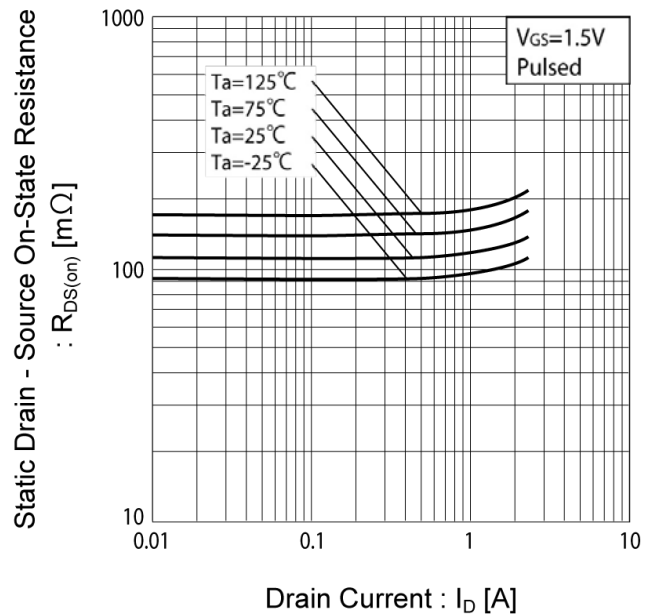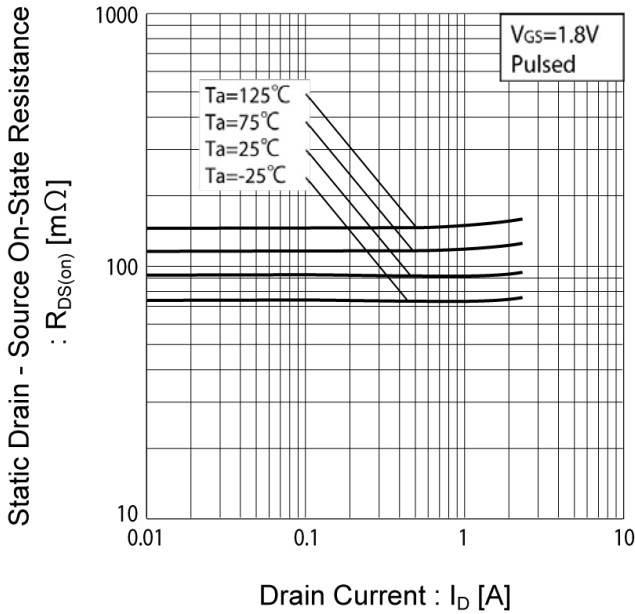Resistance vs. Drain Current (I)

Fig.8 Static Drain - Source On - State
Resistance vs. Drain Current (II)

● **Electrical characteristic curves <MOSFET>**

Fig.9 Static Drain - Source On - State
Resistance vs. Drain Current (III)

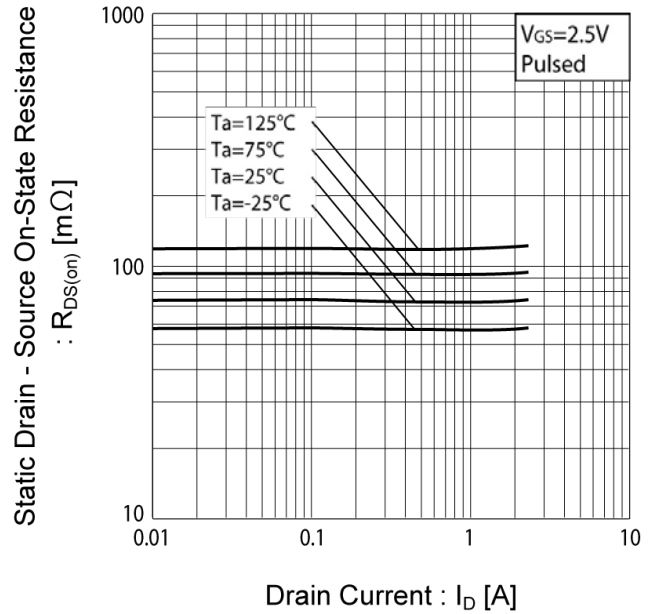Fig.10 Static Drain - Source On - State
Resistance vs. Drain Current (IV)

Fig.11 Static Drain - Source On - State
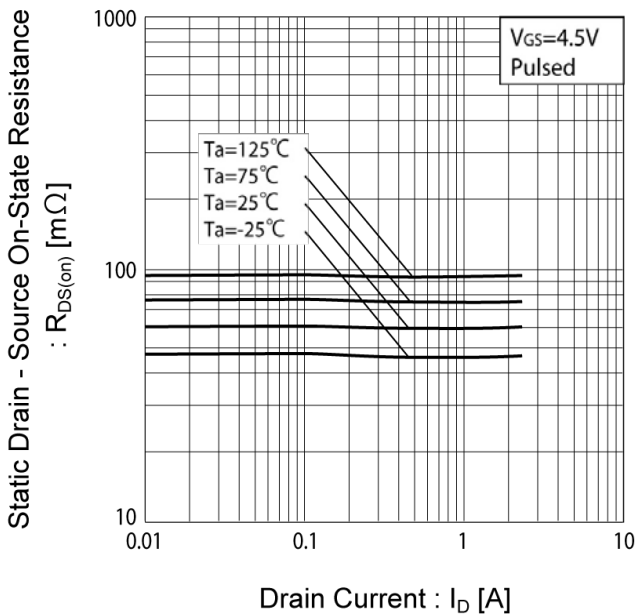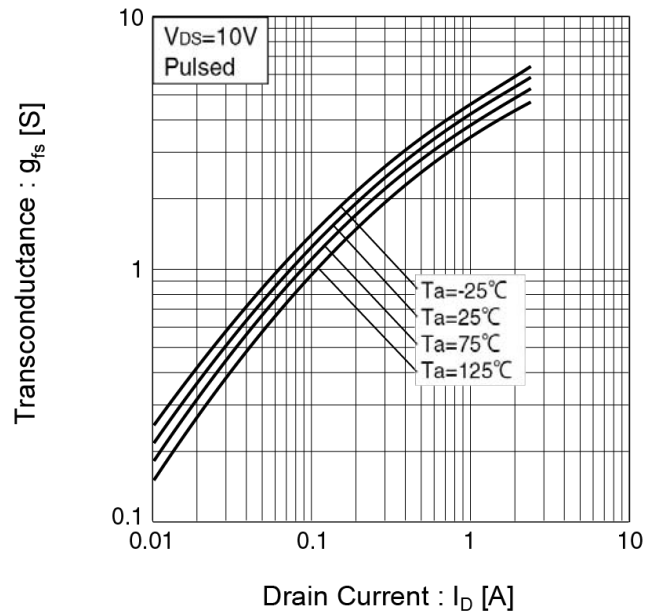Resistance vs. Drain Current (V)

Fig.12 Transconductance vs. Drain
Current

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● **Electrical characteristic curves <SBD>**

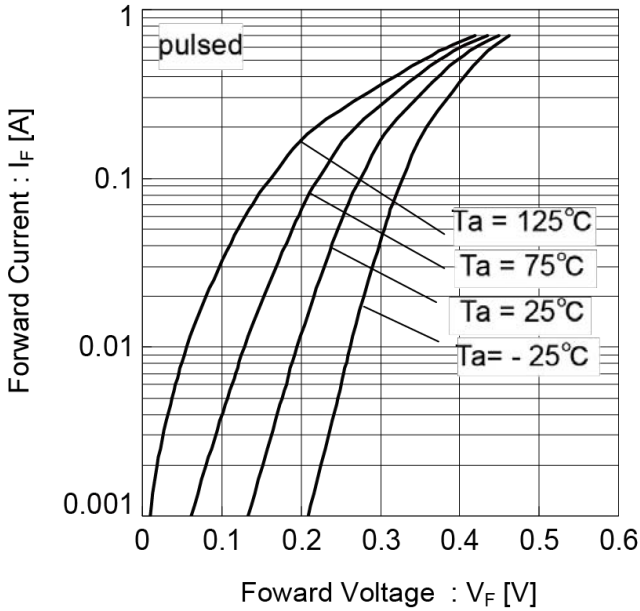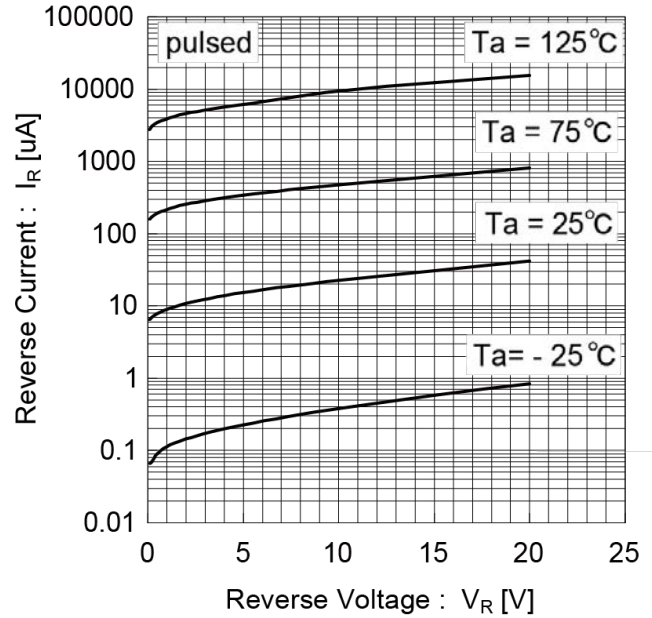Fig.13 Forward Current vs. Forward Voltage

Fig.14 Reverse Current vs. Reverse Voltage

● **Notice**

1. SBD has a large reverse leak current compared to other type of diode. Therefore, it would raise a junction temperature, and increase a reverse power loss. Further rise of inside temperature would cause a thermal runaway. This built-in SBD has low V_F characteristics and therefore, higher leak current. Please consider enough the surrounding temperature, generating heat of MOSFET and the reverse current.

2. This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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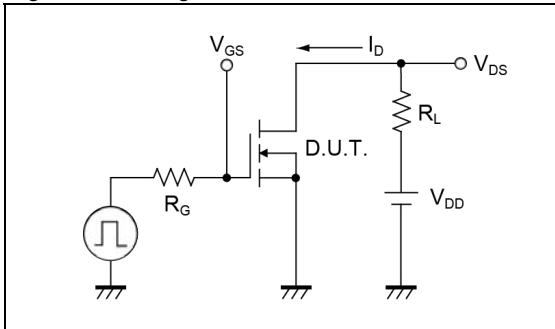● **Measurement circuits**

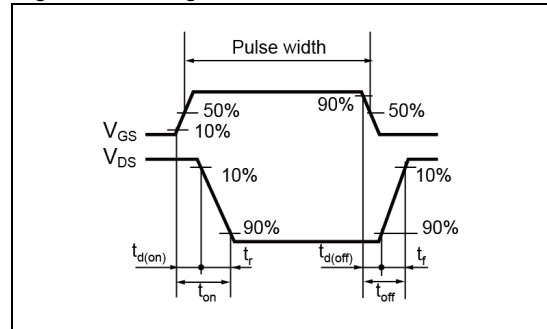Fig.1-1 Switching Time Measurement Circuit

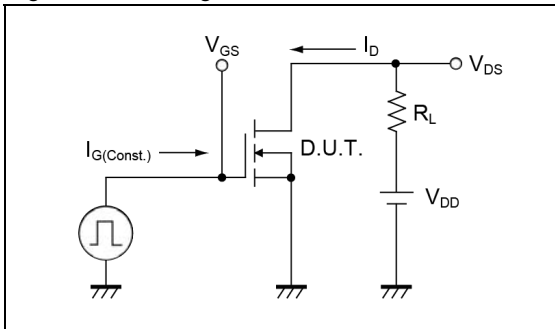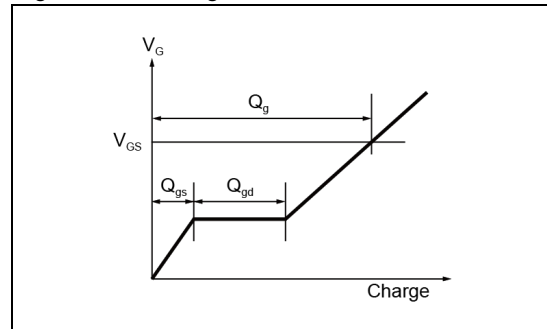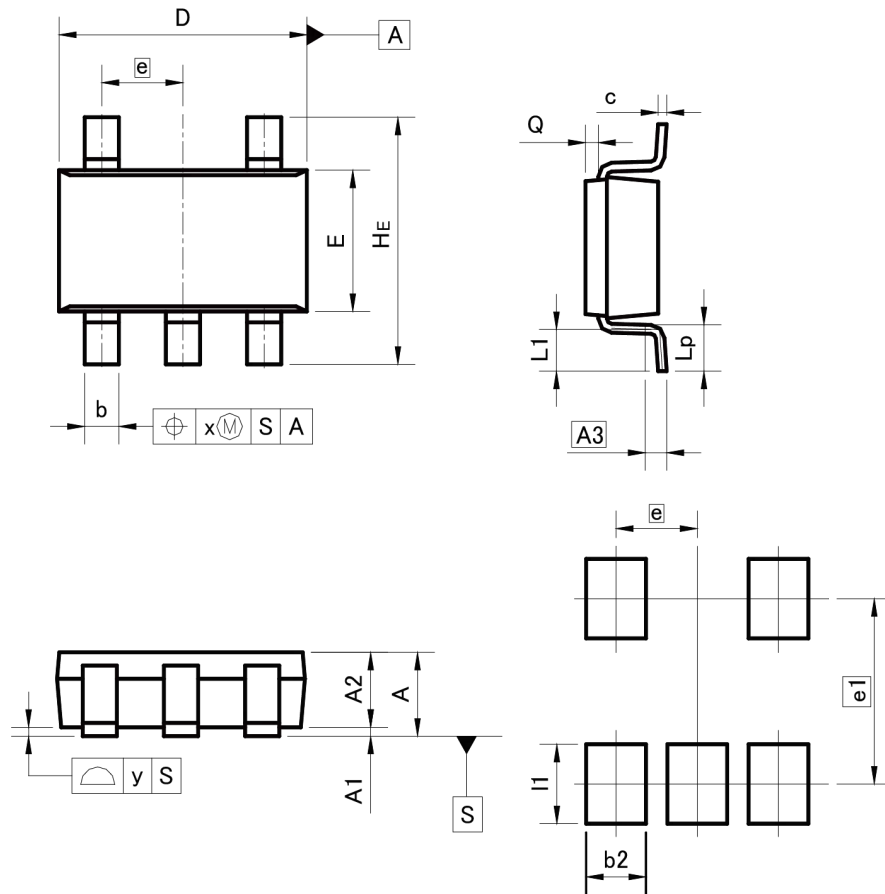Fig.1-2 Switching Waveforms

Fig.2-1 Gate Charge Measurement Circuit

Fig.2-2 Gate Charge Waveform

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●**Dimensions**

TSMT5

Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	–	1.00	–	0.039
A1	0.00	0.10	0.000	0.004
A2	0.75	0.95	0.030	0.037
A3	0.25		0.010	
b	0.35	0.50	0.014	0.020
c	0.10	0.26	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
e	0.95		0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.05	0.25	0.002	0.010
x	–	0.20	–	0.008
y	–	0.10	–	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2		0.70	–	0.028
e1	2.10		0.083	
l1	–	0.90	–	0.035

Dimension in mm/inches

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